

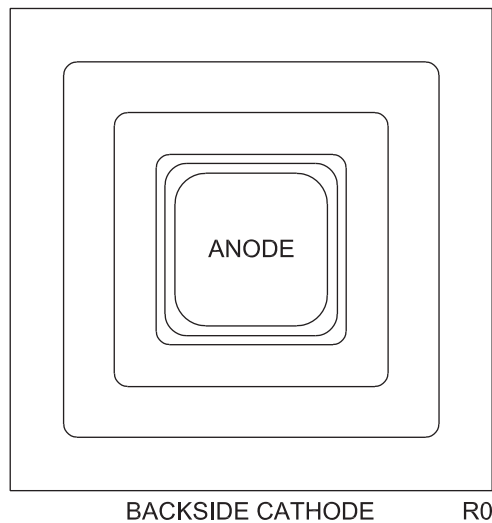
**PROCESS CPD91V**  
**Switching Diode**  
Low Leakage Switching Diode Chip



**PROCESS DETAILS**

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	3.35 x 3.35 MILS
Top Side Metalization	Al - 15,000Å
Back Side Metalization	Au-As - 12,000Å

**GEOMETRY**



**GROSS DIE PER 5 INCH WAFER**  
137,880

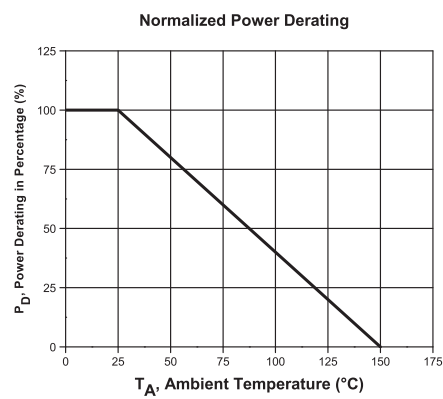
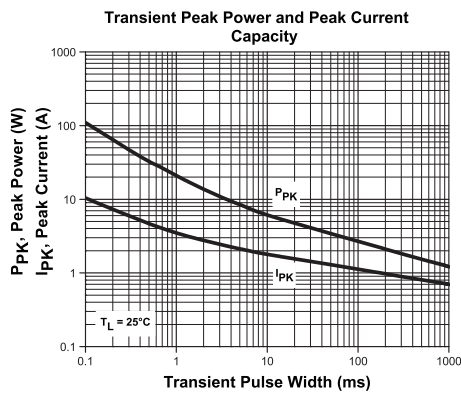
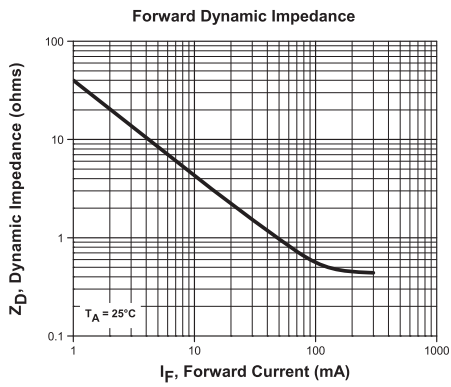
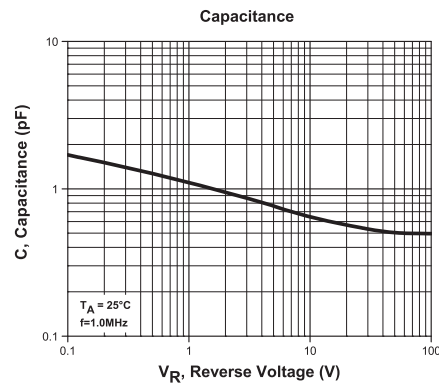
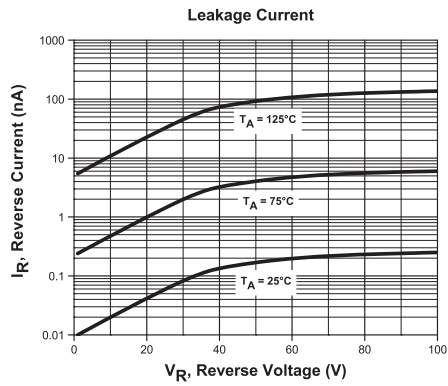
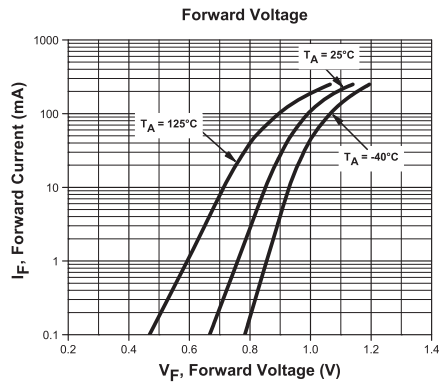
**PRINCIPAL DEVICE TYPES**

- CMPD6001 Series
- CMOD6001
- CMLD6001
- CMLD6001DO
- CMDD6001

R2 (3-August 2010)

# PROCESS CPD91V

## Typical Electrical Characteristics



R2 (3-August 2010)